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# N-Channel 100 V (D-S) MOSFET

| PRODUCT SUMMARY     |                                 |                    |  |  |  |
|---------------------|---------------------------------|--------------------|--|--|--|
| V <sub>DS</sub> (V) | $R_{DS(on)}(\Omega)$            | I <sub>D</sub> (A) |  |  |  |
| 100                 | 0.145 at V <sub>GS</sub> = 10 V | 10                 |  |  |  |

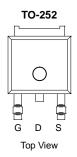
### **FEATURES**

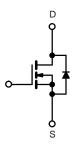
- DT-Trench Power MOSFET
- 175 °C Junction Temperature
- 100 % R<sub>g</sub> Tested



### **APPLICATIONS**

· Primary Side Switch





N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted) |                                   |                 |                  |    |  |  |
|---|-----------------------------------|-----------------|------------------|----|--|--|
| Parameter   | Symbol                            | Limit           | Unit             |    |  |  |
| Drain-Source Voltage  |                                   | V <sub>DS</sub> | 100              |    |  |  |
| Gate-Source Voltage   |                                   | V <sub>GS</sub> | ± 20             | V  |  |  |
| Continuous Drain Current (T <sub>J</sub> = 175 °C) <sup>b</sup>           | T <sub>C</sub> = 25 °C            | l <sub>D</sub>  | 10               |    |  |  |
|   | T <sub>C</sub> = 125 °C           |                 | 5.7              |    |  |  |
| Pulsed Drain Current  | I <sub>DM</sub>                   | 30              | A                |    |  |  |
| Continuous Source Current (Diode Conduction)                              | I <sub>S</sub>                    | 10              |                  |    |  |  |
| Avalanche Current   | I <sub>AR</sub>                   | 10              |                  |    |  |  |
| Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)                            | L = 0.1 mH                        | E <sub>AR</sub> | 12               | mJ |  |  |
| Maximum Power Dissipation   | T <sub>C</sub> = 25 °C            | P <sub>D</sub>  | 55 <sup>b</sup>  | W  |  |  |
|   | T <sub>A</sub> = 25 °C            | ] 'D [          | 2.1 <sup>a</sup> | VV |  |  |
| Operating Junction and Storage Temperature Range                          | T <sub>J</sub> , T <sub>stg</sub> | - 55 to 175     | °C               |    |  |  |

| THERMAL RESISTANCE RATINGS       |              |                     |         |         |      |  |
|----------------------------------|--------------|---------------------|---------|---------|------|--|
| Parameter                        |              | Symbol              | Typical | Maximum | Unit |  |
| lumation to Amelianta            | t ≤ 10 s     | - R <sub>thJA</sub> | 16      | 20      | °C/W |  |
| Junction-to-Ambient <sup>a</sup> | Steady State |                     | 45      | 55      |      |  |
| Junction-to-Case                 |              | R <sub>thJC</sub>   | 2       | 2.4     |      |  |

#### Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.



| Parameter                                     | Symbol              | Test Conditions  | Min. | Typ. <sup>a</sup> | Max.     | Unit |  |
|---|---------------------|--|------|-------------------|----------|------|--|
| Static  |                     |  |      |                   | <u> </u> |      |  |
| Drain-Source Breakdown Voltage                | V <sub>DS</sub>     | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$                          | 100  |                   |          | V    |  |
| Gate Threshold Voltage                        | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$                                   | 1    |                   | 3        | V    |  |
| Gate-Body Leakage                             | I <sub>GSS</sub>    | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$                      |      |                   | ± 100    | nA   |  |
|   |                     | V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V                          |      |                   | 1        |      |  |
| Zero Gate Voltage Drain Current               | I <sub>DSS</sub>    | V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C |      |                   | 50       | μA   |  |
|   |                     | V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C |      |                   | 250      |      |  |
| On-State Drain Current <sup>b</sup>           | I <sub>D(on)</sub>  | V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V                          | 10   |                   |          | Α    |  |
|   |                     | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A                          |      | 0.145             | 0.170    |      |  |
| 5 1 2 2 2 2 1 5 1 1 h                         | D                   | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A, T <sub>J</sub> = 125 °C |      |                   | 0.210    |      |  |
| Drain-Source On-State Resistance <sup>b</sup> | R <sub>DS(on)</sub> | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A, T <sub>J</sub> = 175 °C |      |                   | 0.280    | Ω    |  |
|   |                     |  |      |                   |          |      |  |
| Forward Transconductance <sup>b</sup>         | g <sub>fs</sub>     | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A                          |      | 25                |          | S    |  |
| Dynamic <sup>a</sup>                          |                     |  |      |                   |          |      |  |
| Input Capacitance                             | C <sub>iss</sub>    |  |      | 1206              |          | pF   |  |
| Output Capacitance                            | C <sub>oss</sub>    | $V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$       |      | 215               |          |      |  |
| Reverse Transfer Capacitance                  | C <sub>rss</sub>    |  |      | 75                |          |      |  |
| Total Gate Charge <sup>c</sup>                | $Q_g$               |  |      | 19                | 24       |      |  |
| Gate-Source Charge <sup>c</sup>               | Q <sub>gs</sub>     | $V_{DS} = 80 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 10 \text{A}$    |      | 5.1               |          | nC   |  |
| Gate-Drain Charge <sup>c</sup>                | $Q_{gd}$            |  |      | 7                 |          |      |  |
| Gate Resistance                               | R <sub>g</sub>      |  | 1    |                   | 3.2      | Ω    |  |
| Turn-On Delay Time <sup>c</sup>               | t <sub>d(on)</sub>  |  |      | 8                 | 12       |      |  |
| Rise Time <sup>c</sup>                        | t <sub>r</sub>      | $V_{DD} = 80 \text{ V}, R_L = 5 \Omega$                                |      | 35                | 55       |      |  |
| Turn-Off Delay Time <sup>c</sup>              | t <sub>d(off)</sub> | $I_D \cong 10A, V_{GEN} = 10 \text{ V}, R_G = 2.5 \Omega$              |      | 17                | 25       | ns   |  |
| Fall Time <sup>c</sup>                        | t <sub>f</sub>      |  |      | 30                | 45       |      |  |
| Source-Drain Diode Ratings and Cha            | racteristic (T      | <sub>C</sub> = 25 °C)  |      |                   |          |      |  |
| Pulsed Current                                | I <sub>SM</sub>     |  |      |                   | 10       | Α    |  |
| Diode Forward Voltage <sup>b</sup>            | $V_{SD}$            | I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V                           |      | 0.9               | 1.5      | V    |  |
| Source-Drain Reverse Recovery Time            | t <sub>rr</sub>     | I <sub>F</sub> = 10 A, dI/dt = 100 A/μs                                |      | 55                | 85       | ns   |  |

### Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. Independent of operating temperature.

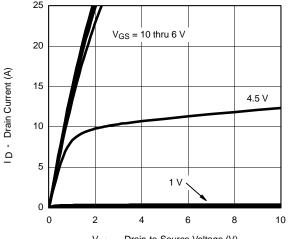
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





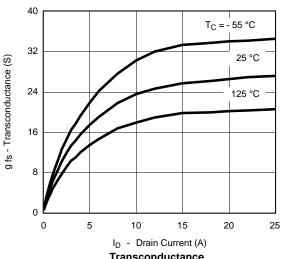
# TYPICAL CHARACTERISTICS (25 °C unless noted)



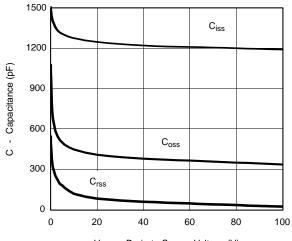


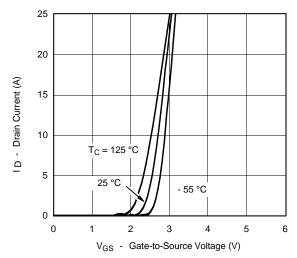
 $V_{DS}\,$  - Drain-to-Source Voltage (V)

### Output Characteristics

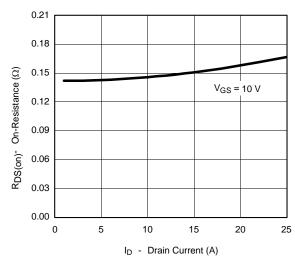


Transconductance

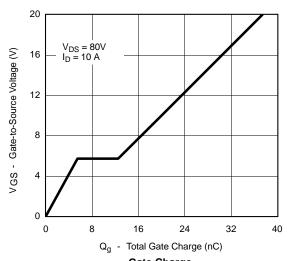




**Transfer Characteristics** 



On-Resistance vs. Drain Current

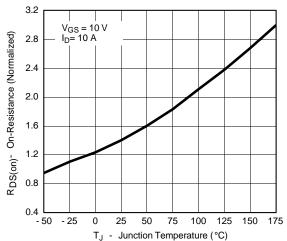


Gate Charge



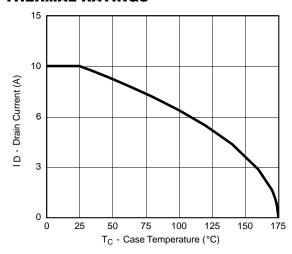
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# TYPICAL CHARACTERISTICS (25 °C unless noted)

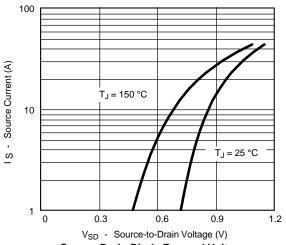


On-Resistance vs. Junction Temperature

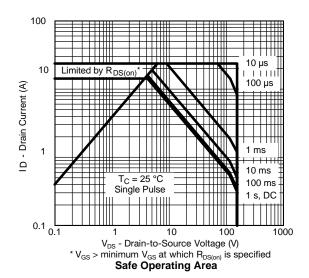
# THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



Source-Drain Diode Forward Voltage

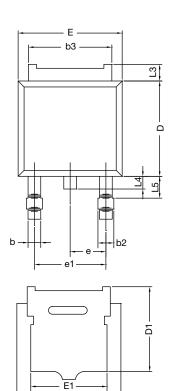


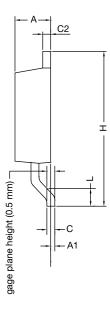
Normalized Thermal Transient Impedance, Junction-to-Case





# **TO-252AA CASE OUTLINE**





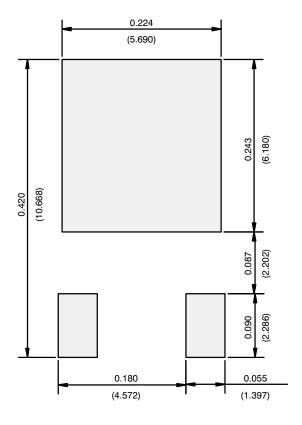
|                                 | MILLIN | METERS   | INCHES    |           |  |  |
|---------------------------------|--------|----------|-----------|-----------|--|--|
| DIM.                            | MIN.   | MAX.     | MIN.      | MAX.      |  |  |
| Α                               | 2.18   | 2.38     | 0.086     | 0.094     |  |  |
| A1                              | -      | 0.127    | -         | 0.005     |  |  |
| b                               | 0.64   | 0.88     | 0.025     | 0.035     |  |  |
| b2                              | 0.76   | 1.14     | 0.030     | 0.045     |  |  |
| b3                              | 4.95   | 5.46     | 0.195     | 0.215     |  |  |
| С                               | 0.46   | 0.61     | 0.018     | 0.024     |  |  |
| C2                              | 0.46   | 0.89     | 0.018     | 0.035     |  |  |
| D                               | 5.97   | 6.22     | 0.235     | 0.245     |  |  |
| D1                              | 5.21   | -        | 0.205     | -         |  |  |
| Е                               | 6.35   | 6.73     | 0.250     | 0.265     |  |  |
| E1                              | 4.32   | -        | 0.170     | -         |  |  |
| Н                               | 9.40   | 10.41    | 0.370     | 0.410     |  |  |
| е                               | 2.28   | BSC      | 0.090 BSC |           |  |  |
| e1                              | 4.56   | 4.56 BSC |           | 0.180 BSC |  |  |
| L                               | 1.40   | 1.78     | 0.055     | 0.070     |  |  |
| L3                              | 0.89   | 1.27     | 0.035     | 0.050     |  |  |
| L4                              | -      | 1.02     | -         | 0.040     |  |  |
| L5                              | 1.14   | 1.52     | 0.045     | 0.060     |  |  |
| ECN: X12-0247-Rev. M, 24-Dec-12 |        |          |           |           |  |  |

### DWG: 5347 Note

• Dimension L3 is for reference only.



# **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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